

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMMC.020AUSAPPLICATION NO.
09/997,396INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(SEE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Hujanen et al.FILING DATE
November 28, 2001GROUP
2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	6,342,277 B1	1/29/02	Sherman			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMMC.020AUS	APPLICATION NO. 09/997,396
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1.	4,058,430	11/15/77	Suntola et al.	156	611	11/25/75
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
DV	3.	WO 00/38191	29.06.00	PCT				
DV	4.	WO 01/88972 A1	22.11.01	PCT				

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DV	5.	Addison, C. C. et al., "The Vapour Pressure of Anhydrous Copper Nitrate, and its Molecular Weight in the Vapour State," <u>J. Chem. Soc.</u> , pp. 3099-3106 (1958).						
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	7.	Bobo, J. F. et al., "Spin-dependent tunneling junctions with hard magnetic layer pinning," <u>Journal of Applied Physics</u> , Vol. 83, No. 11, pp. 6685-6687 (1998).						
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EXAMINER <i>Shuland</i>	DATE CONSIDERED <i>02/20/03</i>
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2818W:\DOCS\ANM\ANM-4150.DOC
110802

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1	6,006,763	12/28/99	Mori et al.			

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